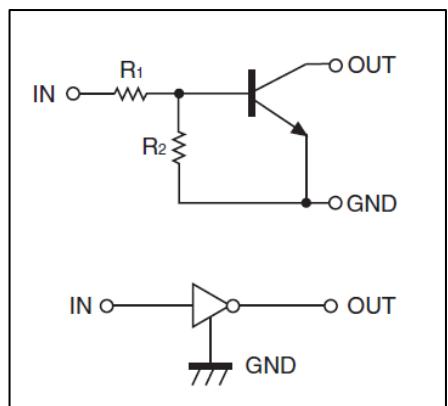


## NPN Silicon Epitaxial Planar Digital Transistor

### FEATURES

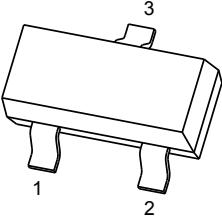
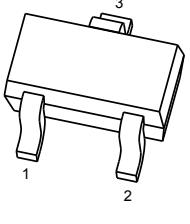
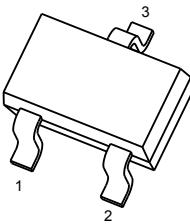
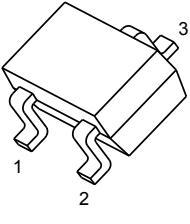
- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit)
- The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completely eliminating parasitic effects
- Only the on/off conditions need to be set for operation, making device designs easy

### Equivalent Circuit



### MARKING: 24

### PIN CONNECTIONS and MARKING

<b>DTC114ECA</b>	<b>SOT-23</b>	<b>DTC114EE</b>	<b>SOT-523</b>
	1. IN 2. GND 3. OUT		1. IN 2. GND 3. OUT
<b>DTC114EUA</b>	<b>SOT-323</b>	<b>DTC114EKA</b>	<b>SOT-23-3L</b>
	1. IN 2. GND 3. OUT		1. IN 2. GND 3. OUT

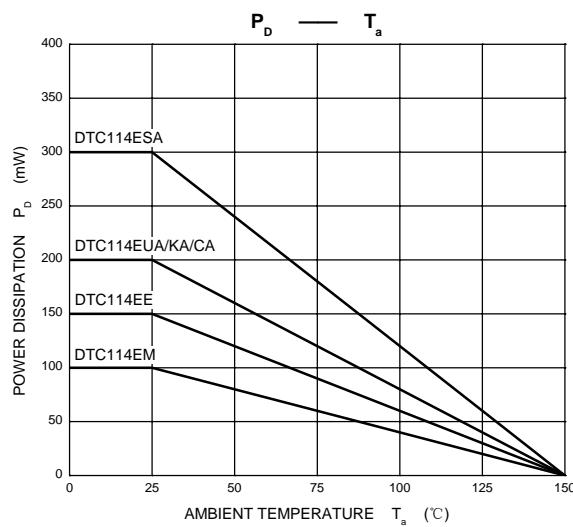
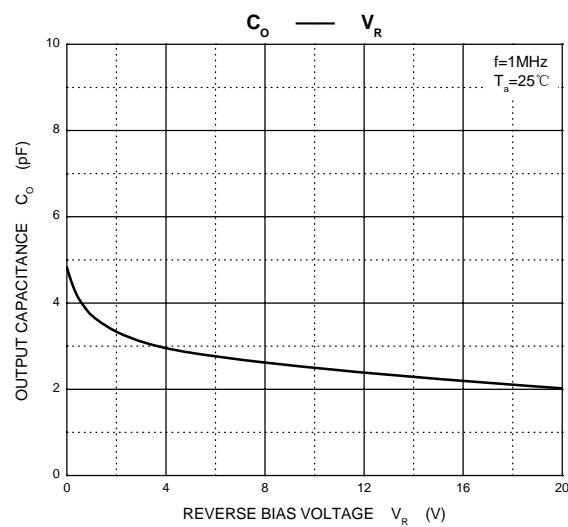
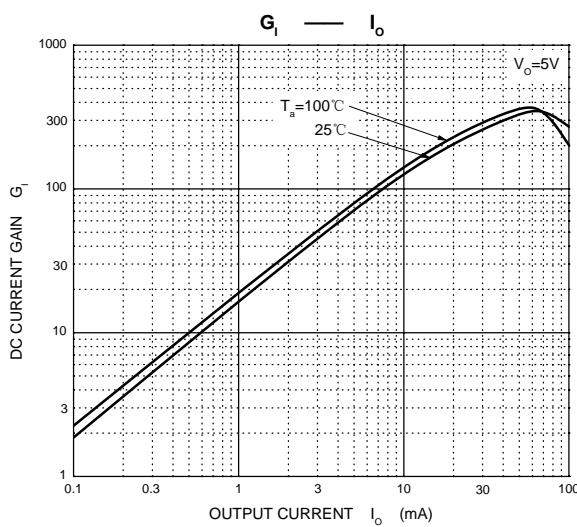
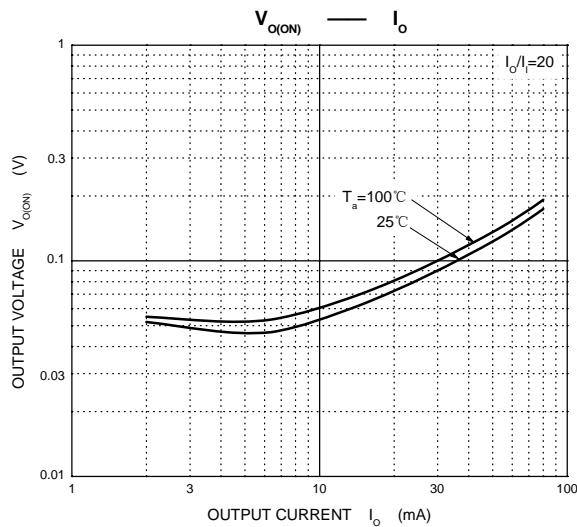
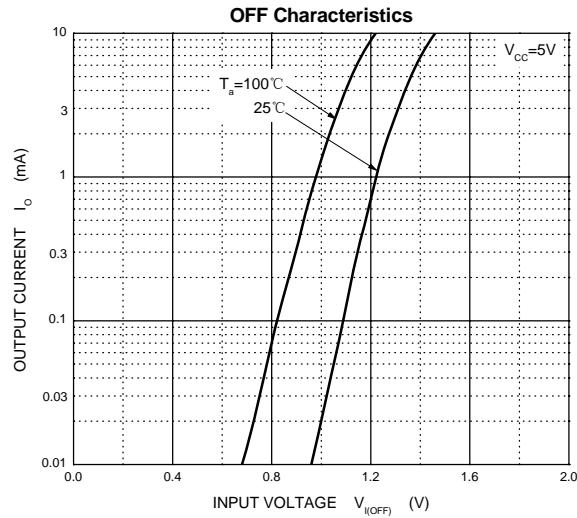
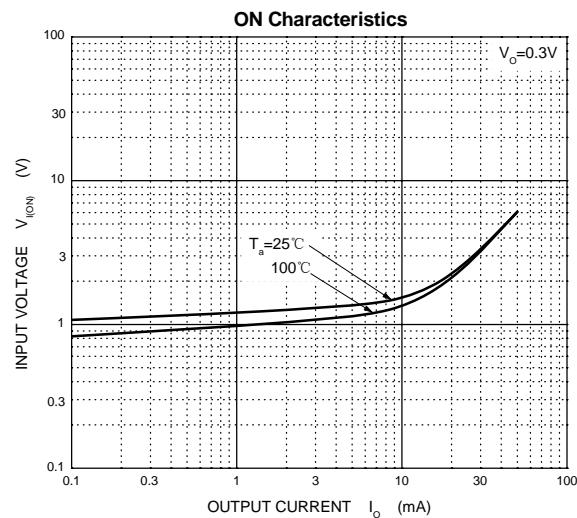
**MAXIMUM RATINGS(Ta=25°C unless otherwise noted)**

Symbol	Parameter	Limits(DTC114E□)						Unit
			E	UA	CA	KA		
V <sub>CC</sub>	Supply Voltage	50						V
V <sub>IN</sub>	Input Voltage	-10~+40						V
I <sub>O</sub>	Output Current	50						mA
I <sub>CM</sub>	Peak Collector Current	100						mA
P <sub>D</sub>	Power Dissipation	150	200	200	200			mW
T <sub>j</sub>	Junction Temperature	150						°C
T <sub>stg</sub>	Storage Temperature	-55~+150						°C

**ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)**

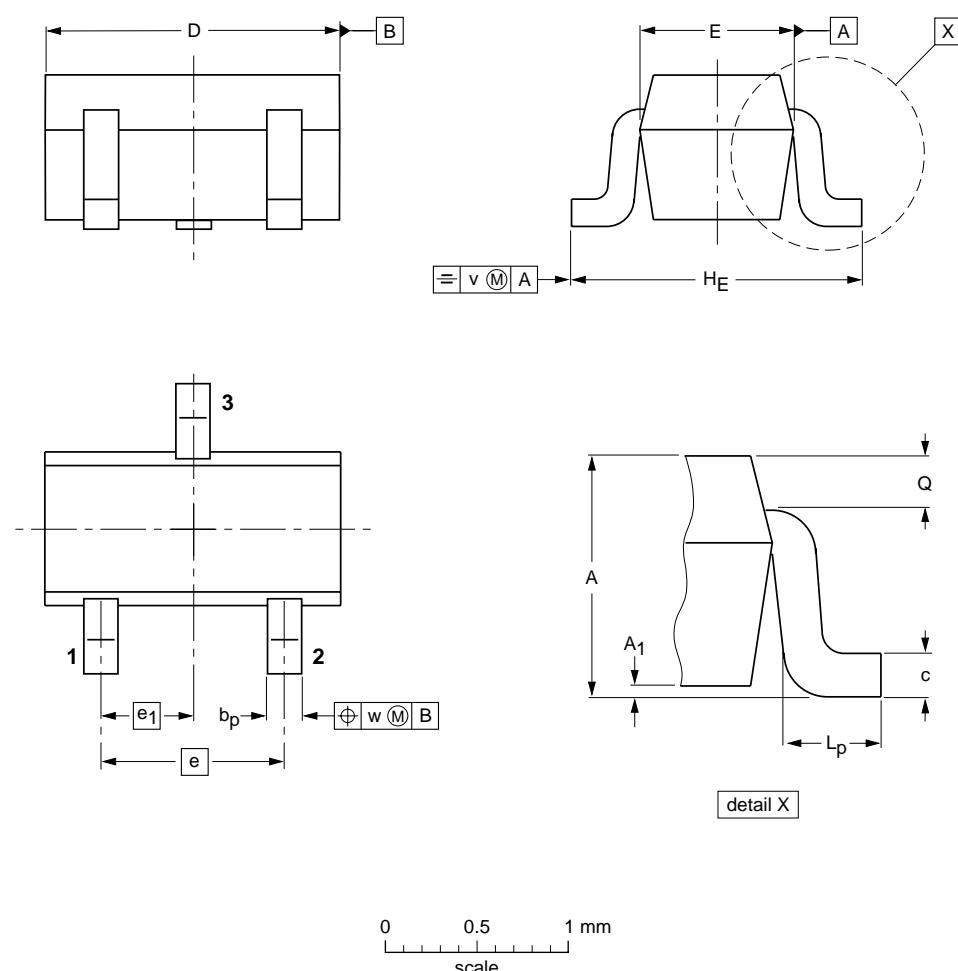
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
<b>Input voltage</b>	V <sub>I(off)</sub>	V <sub>CC</sub> =5V,I <sub>O</sub> =100μA	0.5			V
	V <sub>I(on)</sub>	V <sub>O</sub> =0.3V,I <sub>O</sub> =10mA			3	V
<b>Output voltage</b>	V <sub>O(on)</sub>	I <sub>O</sub> /I <sub>I</sub> =10mA/0.5mA			0.3	V
<b>Input current</b>	I <sub>I</sub>	V <sub>I</sub> =5V			0.88	mA
<b>Output current</b>	I <sub>O(off)</sub>	V <sub>CC</sub> =50V,V <sub>I</sub> =0			0.5	μA
<b>DC current gain</b>	G <sub>I</sub>	V <sub>O</sub> =5V,I <sub>O</sub> =5mA	30			
<b>Input resistance</b>	R <sub>I</sub>		7	10	13	kΩ
<b>Resistance ratio</b>	R <sub>2</sub> /R <sub>1</sub>		0.8	1	1.2	
<b>Transition frequency</b>	f <sub>T</sub>	V <sub>O</sub> =10V,I <sub>O</sub> =5mA,f=100MHz		250		MHz

## TYPICAL CHARACTERISTICS



## PACKAGE OUTLINE

**SOT-523**



**DIMENSIONS (mm are the original dimensions)**

UNIT	A	A <sub>1</sub> max	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	0.95 0.60	0.1	0.30 0.15	0.25 0.10	1.8 1.4	0.9 0.7	1	0.5	1.75 1.45	0.45 0.15	0.23 0.13	0.2	0.2